

# FDP52N20 / FDPF52N20T

## N-Channel MOSFET

200V, 52A, 0.049Ω

### Features

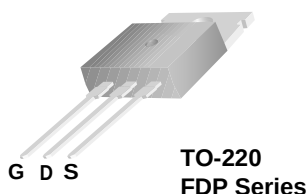
- $R_{DS(on)} = 0.041\Omega$  (Typ.) @  $V_{GS} = 10V$ ,  $I_D = 26A$
- Low gate charge (Typ. 49nC)
- Low  $C_{RSS}$  (Typ. 66pF)
- Fast switching
- 100% avalanche tested
- Improve dv/dt capability
- RoHS compliant



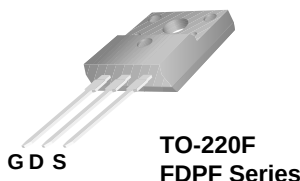
### Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

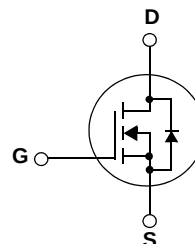
This advance technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switching mode power supplies and active power factor correction.



**TO-220  
FDP Series**



**TO-220F  
FDPF Series**



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter                                                                    | FDP52N20                                  | FDPF52N20T | Units            |
|----------------|------------------------------------------------------------------------------|-------------------------------------------|------------|------------------|
| $V_{DSS}$      | Drain to Source Voltage                                                      | 200                                       |            | V                |
| $V_{GSS}$      | Gate to Source Voltage                                                       | ±30                                       |            | V                |
| $I_D$          | Drain Current                                                                | -Continuous ( $T_C = 25^\circ\text{C}$ )  | 52         | 52*              |
|                |                                                                              | -Continuous ( $T_C = 100^\circ\text{C}$ ) | 33         | 33*              |
| $I_{DM}$       | Drain Current                                                                | - Pulsed (Note 1)                         | 208        | 208*             |
| $E_{AS}$       | Single Pulsed Avalanche Energy                                               | (Note 2)                                  | 2520       | mJ               |
| $I_{AR}$       | Avalanche Current                                                            | (Note 1)                                  | 52         | A                |
| $E_{AR}$       | Repetitive Avalanche Energy                                                  | (Note 1)                                  | 35.7       | mJ               |
| dv/dt          | Peak Diode Recovery dv/dt                                                    | (Note 3)                                  | 4.5        | V/ns             |
| $P_D$          | Power Dissipation                                                            | ( $T_C = 25^\circ\text{C}$ )              | 357        | 38.5             |
|                |                                                                              | - Derate above $25^\circ\text{C}$         | 2.86       | 0.3              |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                                      | -55 to +150                               |            | $^\circ\text{C}$ |
| $T_L$          | Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds | 300                                       |            | $^\circ\text{C}$ |

\*Drain current limited by maximum junction temperature

### Thermal Characteristics

| Symbol          | Parameter                               | FDP52N20 | FDPF52N20T | Units              |
|-----------------|-----------------------------------------|----------|------------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    | 0.35     | 3.3        | $^\circ\text{C/W}$ |
| $R_{\theta CS}$ | Thermal Resistance, Case to Sink Typ.   | 0.5      | -          |                    |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 62.5     | 62.5       |                    |

**Package Marking and Ordering Information**  $T_C = 25^\circ\text{C}$  unless otherwise noted

| Device Marking | Device     | Package | Reel Size | Tape Width | Quantity |
|----------------|------------|---------|-----------|------------|----------|
| FDP52N20       | FDP52N20   | TO-220  | -         | -          | 50       |
| FDPF52N20T     | FDPF52N20T | TO-220F | -         | -          | 50       |

**Electrical Characteristics**

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|--------|-----------|-----------------|------|------|------|-------|
|--------|-----------|-----------------|------|------|------|-------|

**Off Characteristics**

|                                |                                           |                                                                          |     |     |           |                    |
|--------------------------------|-------------------------------------------|--------------------------------------------------------------------------|-----|-----|-----------|--------------------|
| $BV_{DSS}$                     | Drain to Source Breakdown Voltage         | $I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$ , $T_J = 25^\circ\text{C}$ | 200 | -   | -         | V                  |
| $\Delta BV_{DSS} / \Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\mu\text{A}$ , Referenced to $25^\circ\text{C}$                | -   | 0.2 | -         | $V/^\circ\text{C}$ |
| $I_{DSS}$                      | Zero Gate Voltage Drain Current           | $V_{DS} = 200\text{V}$ , $V_{GS} = 0\text{V}$                            | -   | -   | 1         | $\mu\text{A}$      |
|                                |                                           | $V_{DS} = 160\text{V}$ , $T_C = 125^\circ\text{C}$                       | -   | -   | 10        |                    |
| $I_{GSS}$                      | Gate to Body Leakage Current              | $V_{GS} = \pm 30\text{V}$ , $V_{DS} = 0\text{V}$                         | -   | -   | $\pm 100$ | nA                 |

**On Characteristics**

|              |                                      |                                                     |     |       |       |          |
|--------------|--------------------------------------|-----------------------------------------------------|-----|-------|-------|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage               | $V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$          | 3.0 | -     | 5.0   | V        |
| $R_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 10\text{V}$ , $I_D = 26\text{A}$          | -   | 0.041 | 0.049 | $\Omega$ |
| $g_{FS}$     | Forward Transconductance             | $V_{DS} = 40\text{V}$ , $I_D = 26\text{A}$ (Note 4) | -   | 35    | -     | S        |

**Dynamic Characteristics**

|              |                               |                                                                                  |   |      |      |    |
|--------------|-------------------------------|----------------------------------------------------------------------------------|---|------|------|----|
| $C_{iss}$    | Input Capacitance             | $V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$<br>$f = 1\text{MHz}$                | - | 2230 | 2900 | pF |
| $C_{oss}$    | Output Capacitance            |                                                                                  | - | 540  | 700  | pF |
| $C_{rss}$    | Reverse Transfer Capacitance  |                                                                                  | - | 66   | 100  | pF |
| $Q_{g(tot)}$ | Total Gate Charge at 10V      | $V_{DS} = 160\text{V}$ , $I_D = 52\text{A}$<br>$V_{GS} = 10\text{V}$ (Note 4, 5) | - | 49   | 63   | nC |
| $Q_{gs}$     | Gate to Source Gate Charge    |                                                                                  | - | 19   | -    | nC |
| $Q_{gd}$     | Gate to Drain "Miller" Charge |                                                                                  | - | 24   | -    | nC |

**Switching Characteristics**

|              |                     |                                                                             |   |     |     |    |
|--------------|---------------------|-----------------------------------------------------------------------------|---|-----|-----|----|
| $t_{d(on)}$  | Turn-On Delay Time  | $V_{DD} = 100\text{V}$ , $I_D = 20\text{A}$<br>$R_G = 25\Omega$ (Note 4, 5) | - | 53  | 115 | ns |
| $t_r$        | Turn-On Rise Time   |                                                                             | - | 175 | 359 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time |                                                                             | - | 48  | 107 | ns |
| $t_f$        | Turn-Off Fall Time  |                                                                             | - | 29  | 68  | ns |

**Drain-Source Diode Characteristics**

|                 |                                                          |                                             |   |     |     |    |
|-----------------|----------------------------------------------------------|---------------------------------------------|---|-----|-----|----|
| I <sub>S</sub>  | Maximum Continuous Drain to Source Diode Forward Current |                                             | - | -   | 52  | A  |
| I <sub>SM</sub> | Maximum Pulsed Drain to Source Diode Forward Current     |                                             | - | -   | 204 | A  |
| V <sub>SD</sub> | Drain to Source Diode Forward Voltage                    | V <sub>GS</sub> = 0V, I <sub>SD</sub> = 52A | - | -   | 1.5 | V  |
| t <sub>rr</sub> | Reverse Recovery Time                                    | V <sub>GS</sub> = 0V, I <sub>SD</sub> = 52A | - | 162 | -   | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                                  | di <sub>F</sub> /dt = 100A/μs (Note 4)      | - | 1.3 | -   | μC |

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $L = 1.4\text{mH}$ ,  $I_{AS} = 52\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 52\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

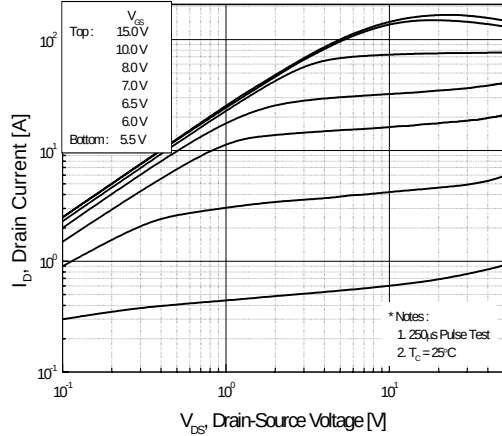


Figure 2. Transfer Characteristics

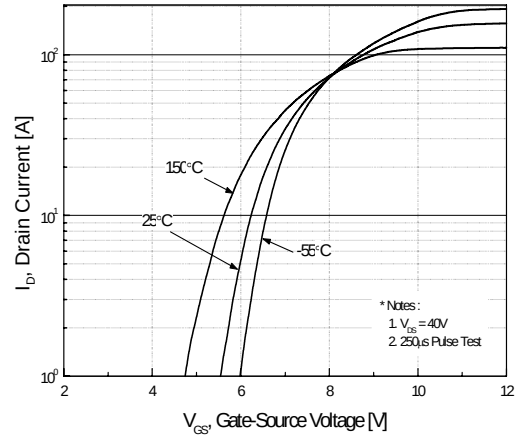


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

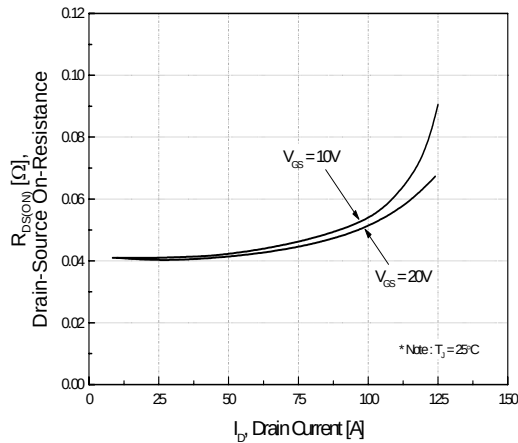


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

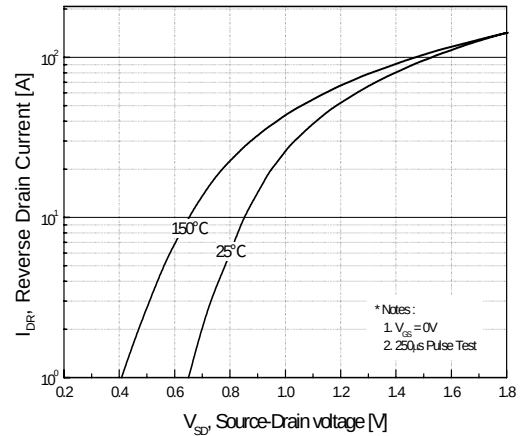


Figure 5. Capacitance Characteristics

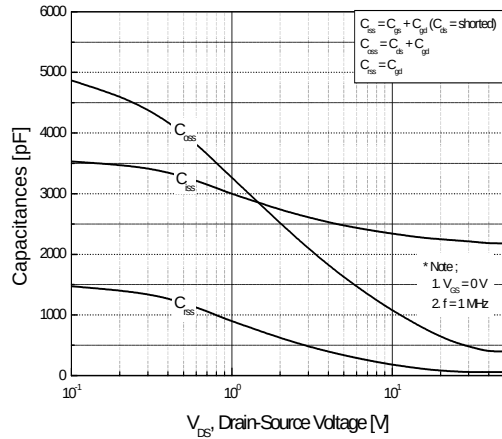
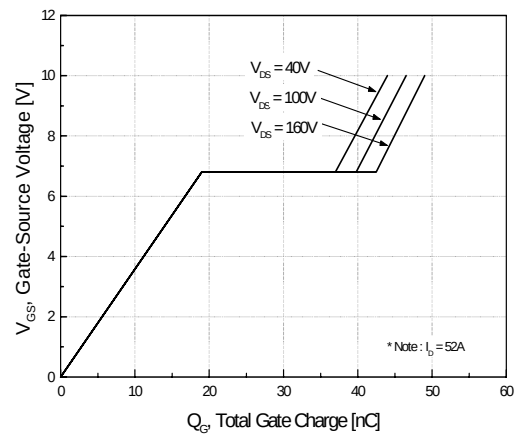
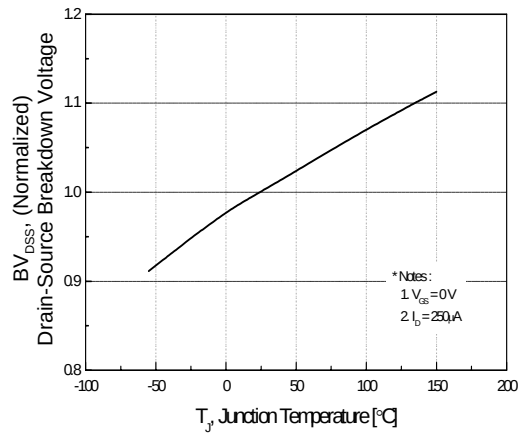


Figure 6. Gate Charge Characteristics

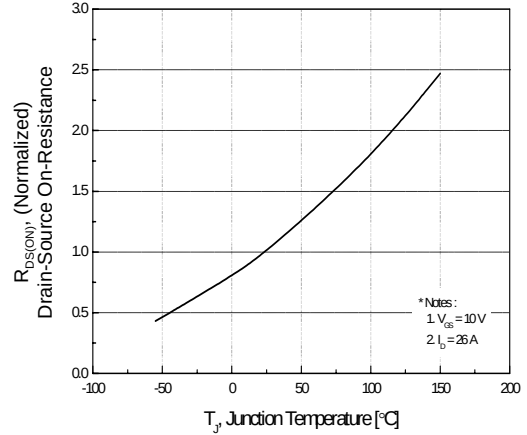


## Typical Performance Characteristics (Continued)

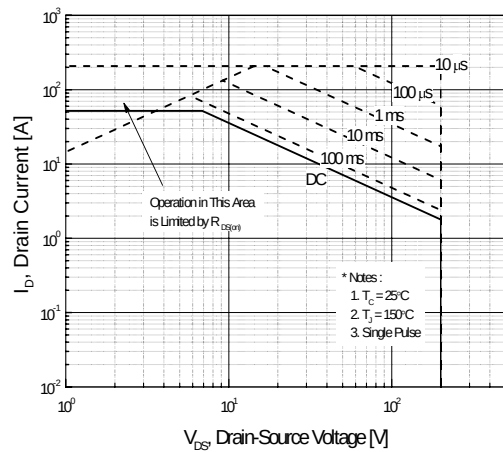
**Figure 7. Breakdown Voltage Variation vs. Temperature**



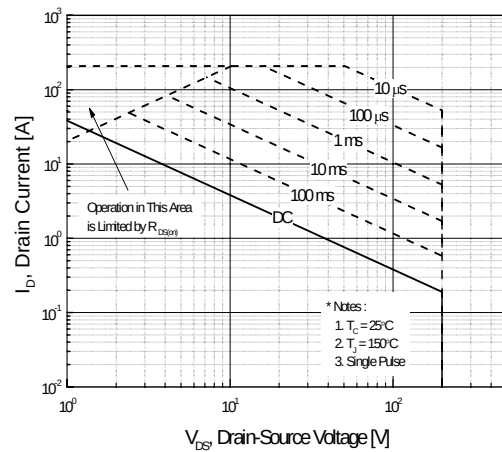
**Figure 8. On-Resistance Variation vs. Temperature**



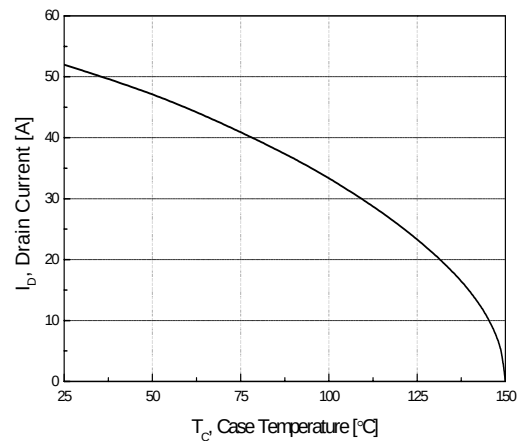
**Figure 9-1. Maximum Safe Operating Area - FDP52N20**



**Figure 9-2. Maximum Safe Operating Area - FDPF52N20T**



**Figure 10. Maximum Drain Current**



# Typical Performance Characteristics (Continued)

Figure 11-1. Transient Thermal Response Curve - FDP52N20

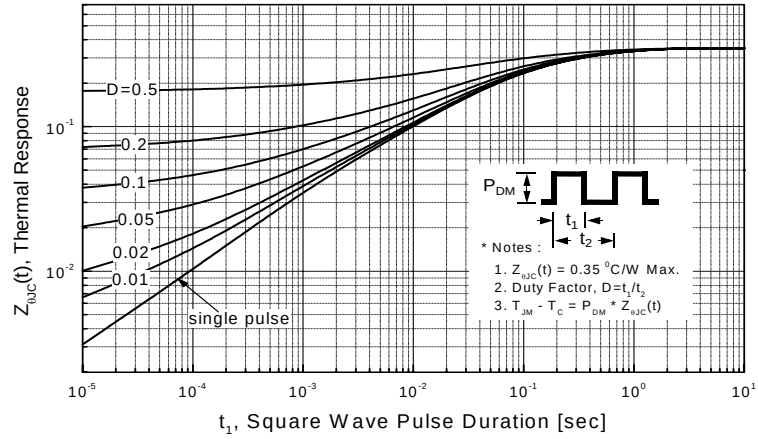
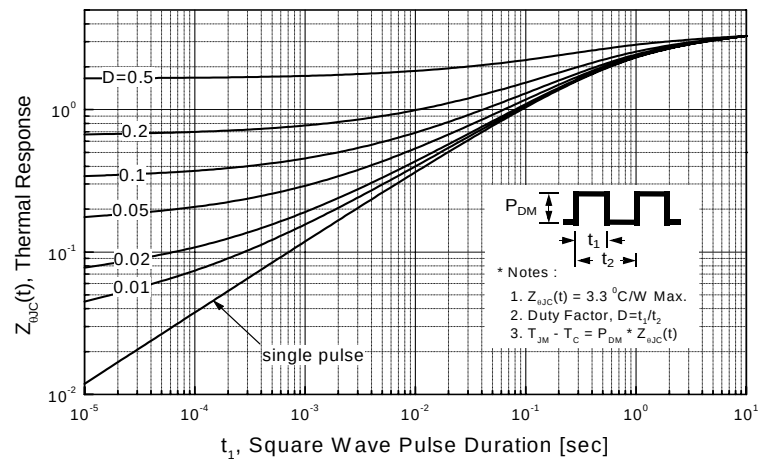
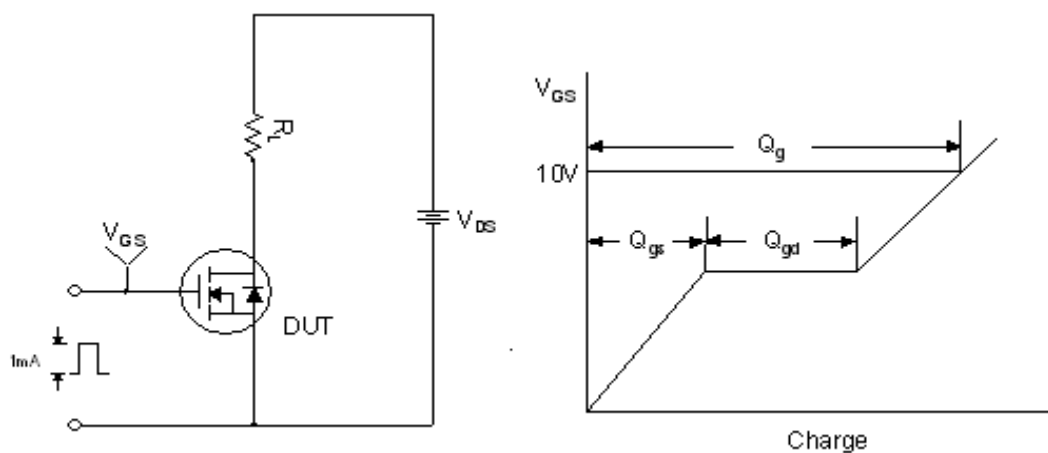


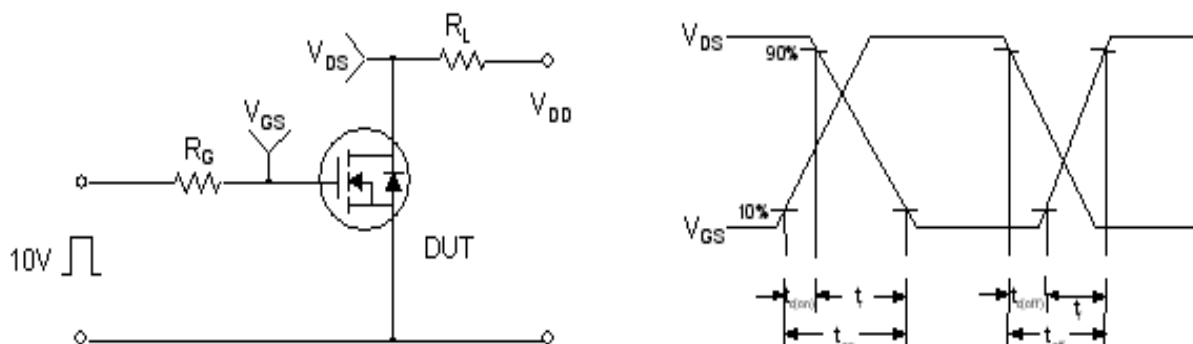
Figure 11-2. Transient Thermal Response Curve - FDPF52N20T



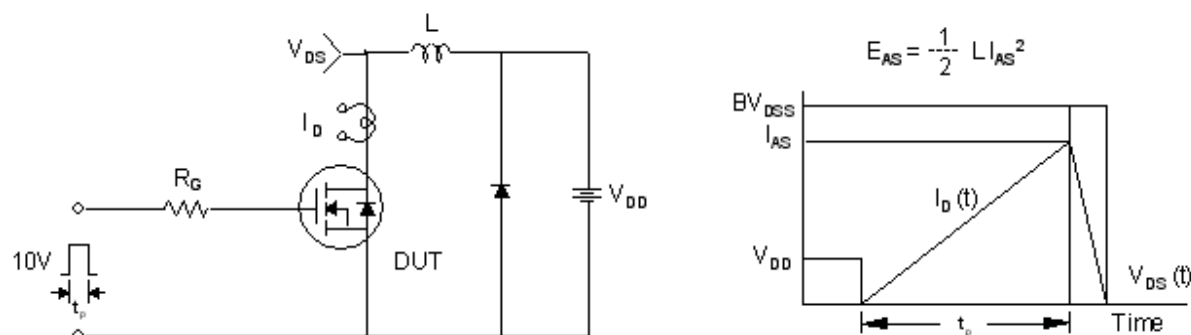
Gate Charge Test Circuit & Waveform



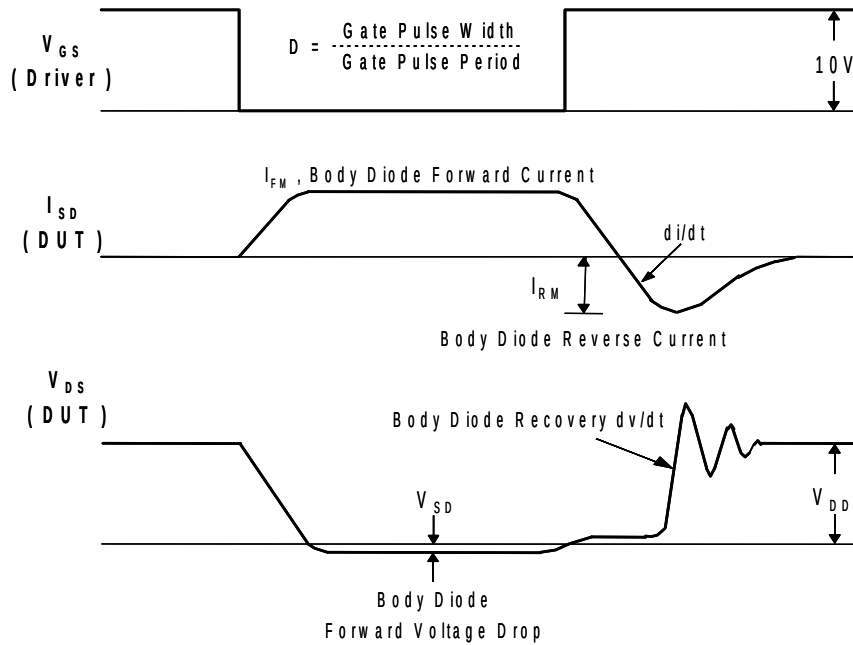
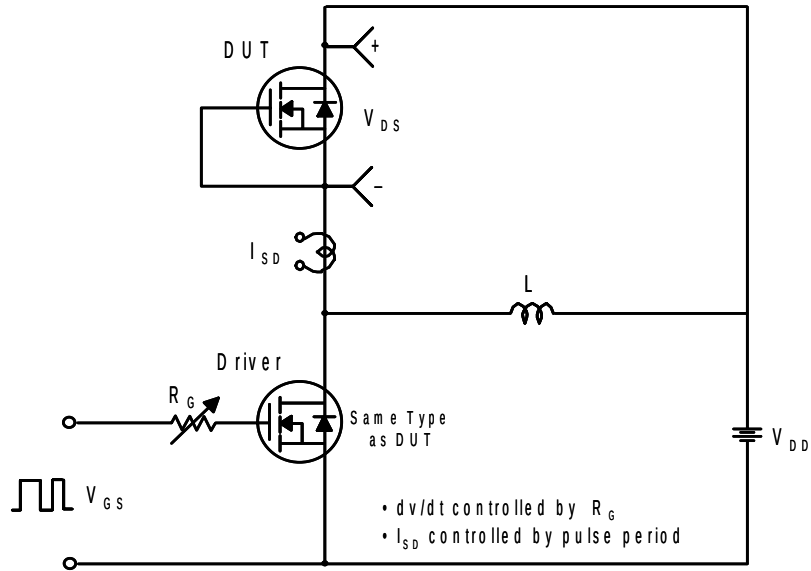
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

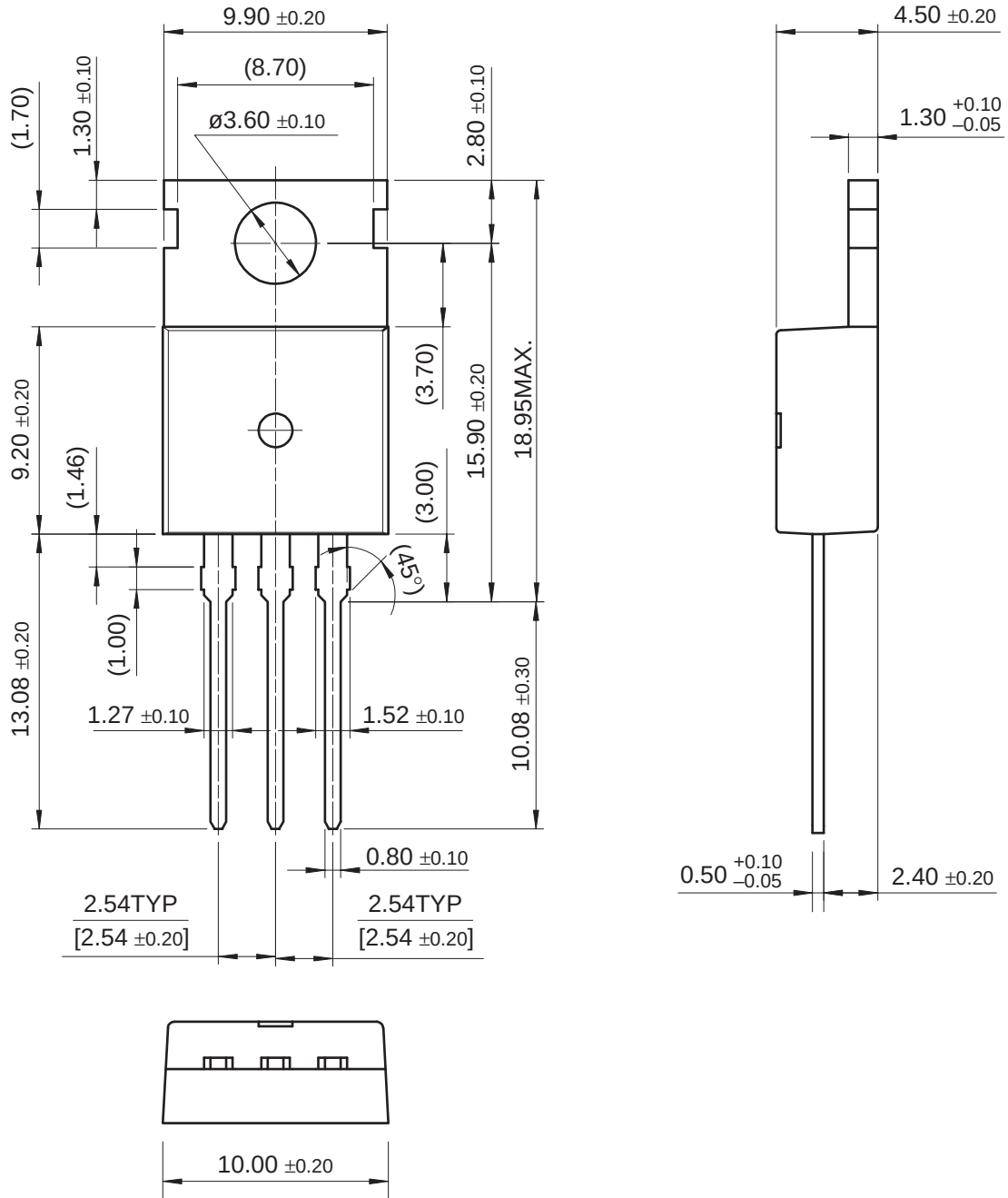


# Peak Diode Recovery dv/dt Test Circuit & Waveforms



# Mechanical Dimensions

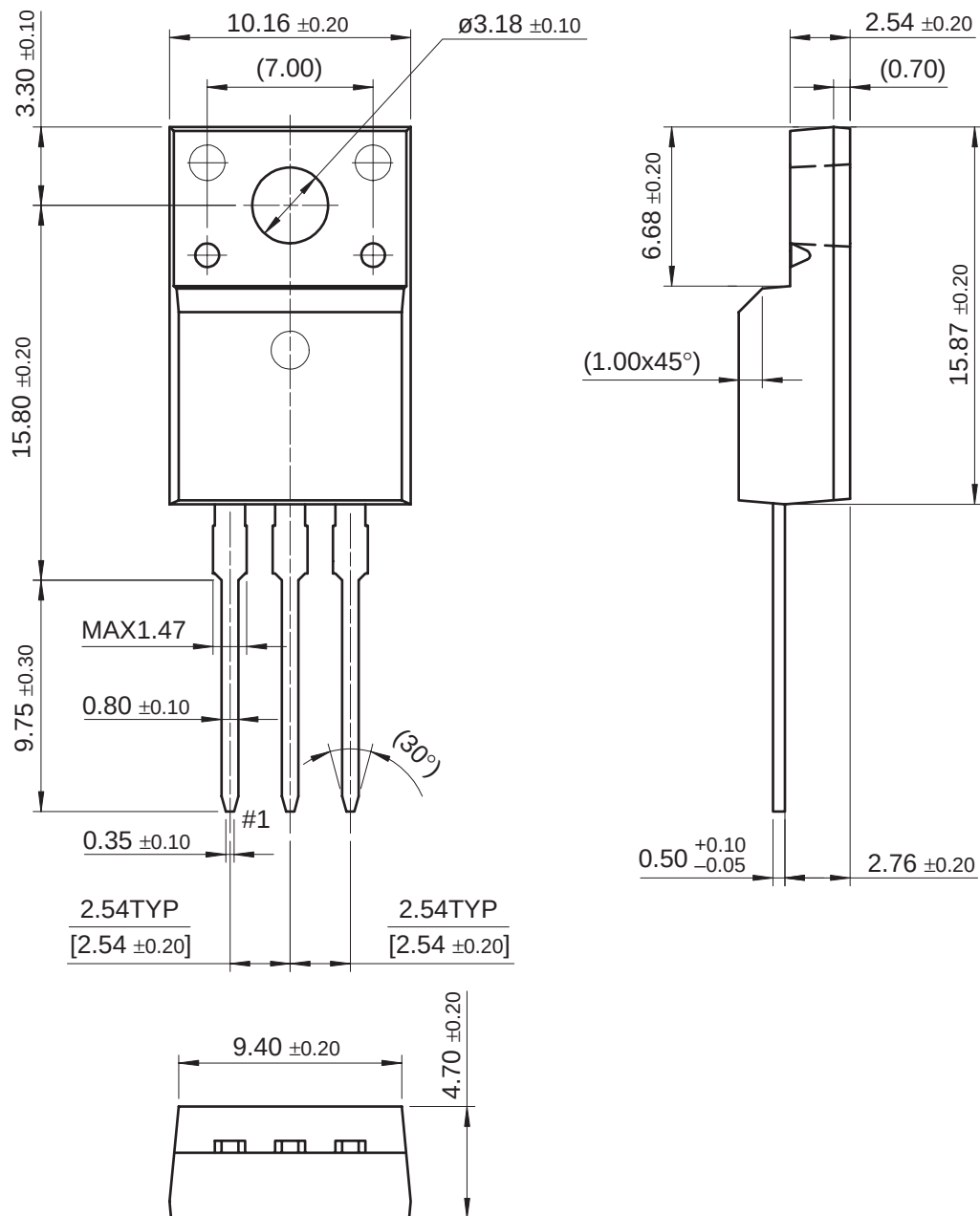
## TO-220





# Mechanical Dimensions

## TO-220F



Dimensions in Millimeters



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| FPS™                     |                      | SuperSOT™-3                | VCX™                 |
| FRFET®                   | PDP-SPM™             | SuperSOT™-6                |                      |
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